

## Weebit Nano and Leti file joint patent for multi-level programming

**27 August 2020** – Weebit Nano (ASX: WBT), a leading developer of next-generation memory technology for the global semiconductor industry, and its development partner Leti, the French research institute recognised as a global leader in the field of micro-electronics, filed a new patent to further protect the intellectual property of its silicon oxide (SiOx) ReRAM technology.

The new patent defines an efficient method to implement robust multi-level storage in ReRAM. Multi-level is the ability to store more than one bit per cell, thus increasing the memory storage capacity without increasing the number of memory cells or the memory array size, making the memory much more cost-efficient.

This patent uses the variability characteristics of ReRAM memory cells to increase the number of resistance levels that can be tuned by the ReRAM. While this method is based on Weebit Nano's SiOx-based ReRAM, importantly, it can also be extended to any ReRAM technology.

**Coby Hanoch, CEO of Weebit Nano**, said: "Our close collaboration with our partners at Leti has allowed us to develop a method that is an important step in creating a multi-level cell which can significantly improve our cost-competitiveness. In parallel to the ongoing productisation activity we are continuing to improve the technology to make it even more attractive to customers."

This announcement has been authorised for release by the Board.

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### About Weebit Nano Limited

Weebit Nano is a leader in the development of next generation computer memory technology and plans to become the new industry standard in this space. Its goal is to address the growing need for a significantly higher performance and lower power computer memory technology. Weebit Nano's ReRAM technology is based on fab-friendly Silicon Oxide, allowing the company to rapidly execute, without the need for special equipment or preparations. The company secured several patents to ensure optimal commercial and legal protection for its ground-breaking technology.

Weebit Nano's technology enables a quantum leap, allowing semiconductor memory elements to be significantly cheaper, faster, more reliable and more energy efficient than the existing Flash technology. Weebit Nano has signed an R&D agreement with Leti, an R&D institute that specialises in nanotechnologies, to further develop SiOx ReRAM technology.

For more information please visit: <http://www.weebit-nano.com/>



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